

## Photo Transistor Chip

### Features

- Light Activated Photo Transistor Chip
- Planar NPN
- Aluminum Wire bondable
- Backside Metallization - Gold
- Die Attach methods: Eutectic or Epoxy

### Electrical Characteristics @ 25°C

SYMBOL	CHARACTERISTIC	CONDITIONS	MIN	TYP	MAX	UNITS
$BV_{CEO}$	Collector-Emitter Voltage	$I_C = 100 \mu A$		500		Volts
$BV_{EBO}$	Emitter-Base Voltage	$I_E = 100 \mu A$		20		Volts
$BV_{CBO}$	Collector-Base Voltage	$I_C = 100 \mu A$		500		Volts
ID	Collector Current	$V_{CE} = 10$ Volts		30		nAmps
$h_{FE}$	Beta	$V_{CE} = 5$ Volts, $I_C = 1$ mA		25		